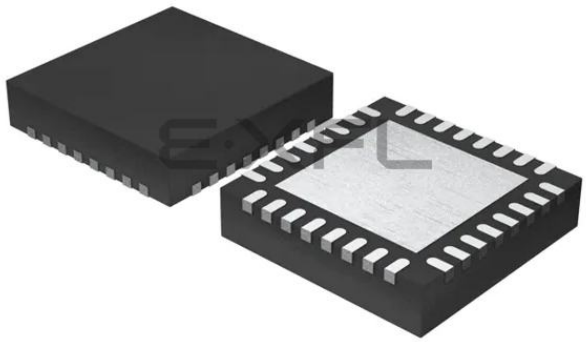

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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Discontinued at Digi-Key
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	24MHz
Connectivity	EBI/EMI, I²C, IrDA, SmartCard, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, I²S, POR, PWM, WDT
Number of I/O	24
Program Memory Size	4KB (4K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	2K x 8
Voltage - Supply (Vcc/Vdd)	1.98V ~ 3.8V
Data Converters	A/D 4x12b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	32-VQFN Exposed Pad
Supplier Device Package	32-QFN (6x6)
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/efm32zg210f4-qfn32

1 Ordering Information

Table 1.1 (p. 2) shows the available EFM32ZG210 devices.

Table 1.1. Ordering Information

Ordering Code	Flash (kB)	RAM (kB)	Max Speed (MHz)	Supply Voltage (V)	Temperature (ºC)	Package
EFM32ZG210F4-QFN32	4	2	24	1.98 - 3.8	-40 - 85	QFN32
EFM32ZG210F8-QFN32	8	2	24	1.98 - 3.8	-40 - 85	QFN32
EFM32ZG210F16-QFN32	16	4	24	1.98 - 3.8	-40 - 85	QFN32
EFM32ZG210F32-QFN32	32	4	24	1.98 - 3.8	-40 - 85	QFN32

Visit **www.silabs.com** for information on global distributors and representatives.

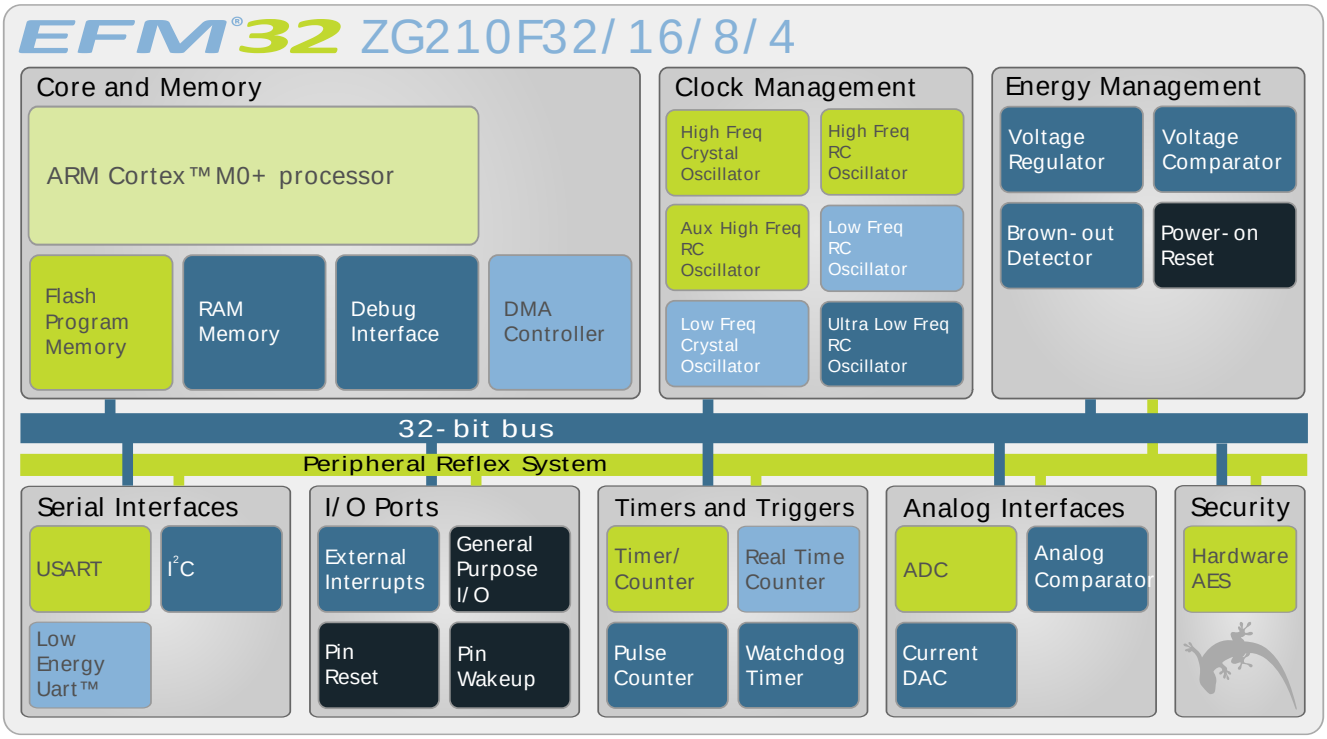
2 System Summary

2.1 System Introduction

The EFM32 MCUs are the world's most energy friendly microcontrollers. With a unique combination of the powerful 32-bit ARM Cortex-M0+, innovative low energy techniques, short wake-up time from energy saving modes, and a wide selection of peripherals, the EFM32ZG microcontroller is well suited for any battery operated application as well as other systems requiring high performance and low-energy consumption. This section gives a short introduction to each of the modules in general terms and also shows a summary of the configuration for the EFM32ZG210 devices. For a complete feature set and in-depth information on the modules, the reader is referred to the *EFM32ZG Reference Manual*.

A block diagram of the EFM32ZG210 is shown in Figure 2.1 (p. 3) .

Figure 2.1. Block Diagram



2.1.1 ARM Cortex-M0+ Core

The ARM Cortex-M0+ includes a 32-bit RISC processor which can achieve as much as 0.9 Dhrystone MIPS/MHz. A Wake-up Interrupt Controller handling interrupts triggered while the CPU is asleep is included as well. The EFM32 implementation of the Cortex-M0+ is described in detail in *ARM Cortex-M0+ Devices Generic User Guide*.

2.1.2 Debug Interface (DBG)

This device includes hardware debug support through a 2-pin serial-wire debug interface .

2.1.3 Memory System Controller (MSC)

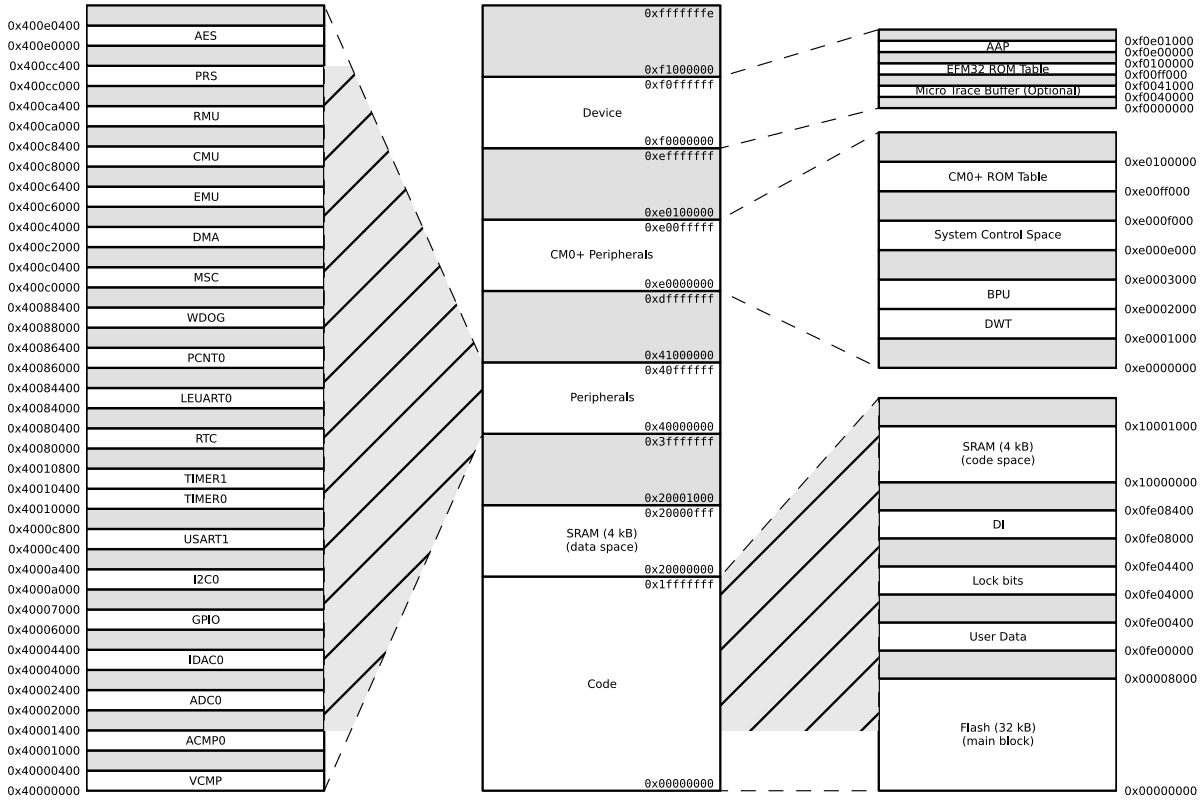
The Memory System Controller (MSC) is the program memory unit of the EFM32ZG microcontroller. The flash memory is readable and writable from both the Cortex-M0+ and DMA. The flash memory is divided into two blocks; the main block and the information block. Program code is normally written to the main block. Additionally, the information block is available for special user data and flash lock bits. There is also a read-only page in the information block containing system and device calibration data. Read and write operations are supported in the energy modes EM0 and EM1.

Module	Configuration	Pin Connections
GPIO	24 pins	Available pins are shown in Table 4.3 (p. 54)

2.3 Memory Map

The *EFM32ZG210* memory map is shown in Figure 2.2 (p. 7), with RAM and Flash sizes for the largest memory configuration.

Figure 2.2. EFM32ZG210 Memory Map with largest RAM and Flash sizes



3 Electrical Characteristics

3.1 Test Conditions

3.1.1 Typical Values

The typical data are based on T_{AMB}=25°C and V_{DD}=3.0 V, as defined in Table 3.2 (p. 8), by simulation and/or technology characterisation unless otherwise specified.

3.1.2 Minimum and Maximum Values

The minimum and maximum values represent the worst conditions of ambient temperature, supply voltage and frequencies, as defined in Table 3.2 (p. 8), by simulation and/or technology characterisation unless otherwise specified.

3.2 Absolute Maximum Ratings

The absolute maximum ratings are stress ratings, and functional operation under such conditions are not guaranteed. Stress beyond the limits specified in Table 3.1 (p. 8) may affect the device reliability or cause permanent damage to the device. Functional operating conditions are given in Table 3.2 (p. 8) .

Table 3.1. Absolute Maximum Ratings

Symbol	Parameter	Condition	Min	Typ	Max	Unit
T_{STG}	Storage temperature range		-40		150[1]	°C
T_S	Maximum soldering temperature	Latest IPC/JEDEC J-STD-020 Standard			260	°C
V_{DDMAX}	External main supply voltage		0		3.8	V
V_{IOPIN}	Voltage on any I/O pin		-0.3		V_{DD}+0.3	V

[1]Based on programmed devices tested for 10000 hours at 150ºC. Storage temperature affects retention of preprogrammed calibration values stored in flash. Please refer to the Flash section in the Electrical Characteristics for information on flash data retention for different temperatures.

3.3 General Operating Conditions

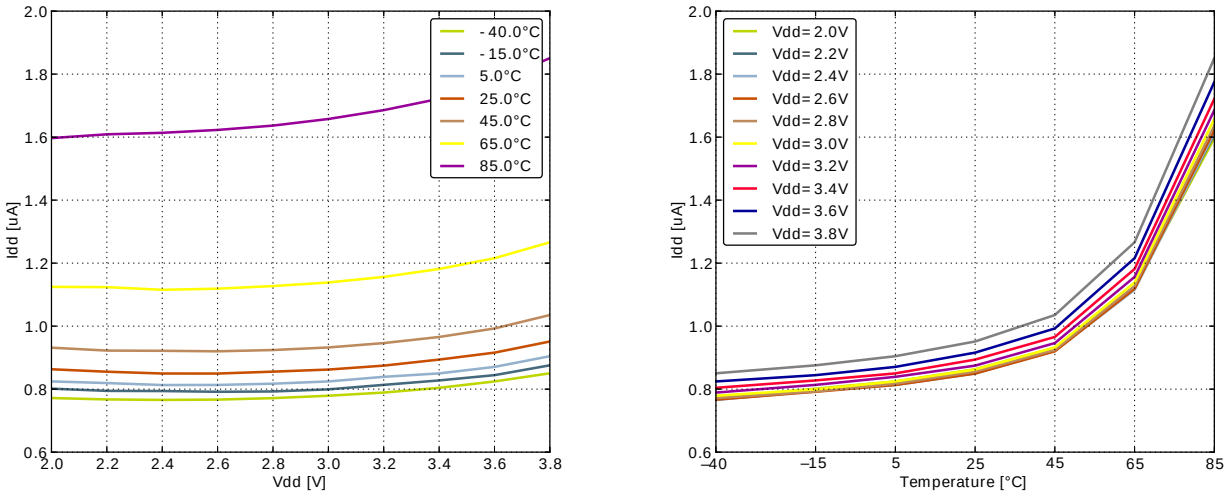
3.3.1 General Operating Conditions

Table 3.2. General Operating Conditions

Symbol	Parameter	Min	Typ	Max	Unit
T_{AMB}	Ambient temperature range	-40		85	°C
V_{DDOP}	Operating supply voltage	1.98		3.8	V
f_{APB}	Internal APB clock frequency			24	MHz
f_{AHB}	Internal AHB clock frequency			24	MHz

3.4.3 EM2 Current Consumption

Figure 3.11. EM2 current consumption. RTC prescaled to 1kHz, 32.768 kHz LFRCO.



3.4.4 EM3 Current Consumption

Figure 3.12. EM3 current consumption.

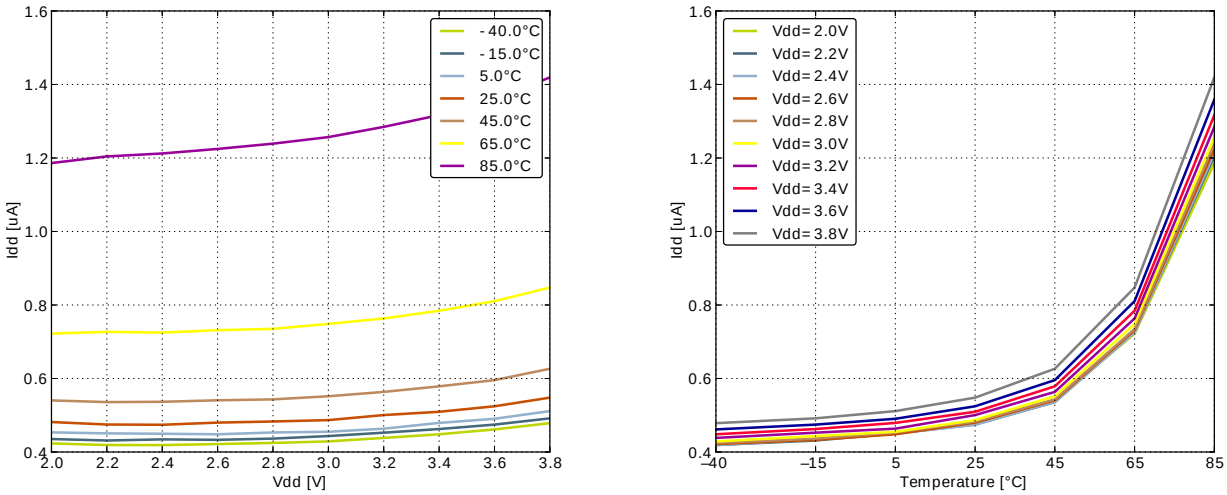


Table 3.5. Power Management

Symbol	Parameter	Condition	Min	Typ	Max	Unit
$V_{BODextthr-}$	BOD threshold on falling external supply voltage		1.74		1.96	V
$V_{BODextthr+}$	BOD threshold on rising external supply voltage			1.85		V
t_{RESET}	Delay from reset is released until program execution starts	Applies to Power-on Reset, Brown-out Reset and pin reset.		163		µs
$C_{DECOUPLE}$	Voltage regulator decoupling capacitor.	X5R capacitor recommended. Apply between DECOUPLE pin and GROUND		1		µF

3.7 Flash

Table 3.6. Flash

Symbol	Parameter	Condition	Min	Typ	Max	Unit
EC_{FLASH}	Flash erase cycles before failure		20000			cycles
RET_{FLASH}	Flash data retention	T_{AMB}<150°C	10000			h
		T_{AMB}<85°C	10			years
		T_{AMB}<70°C	20			years
t_{W_PROG}	Word (32-bit) programming time		20			µs
t_{P_ERASE}	Page erase time		20	20.4	20.8	ms
t_{D_ERASE}	Device erase time		40	40.8	41.6	ms
I_{ERASE}	Erase current				7[1]	mA
I_{WRITE}	Write current				7[1]	mA
V_{FLASH}	Supply voltage during flash erase and write		1.98		3.8	V

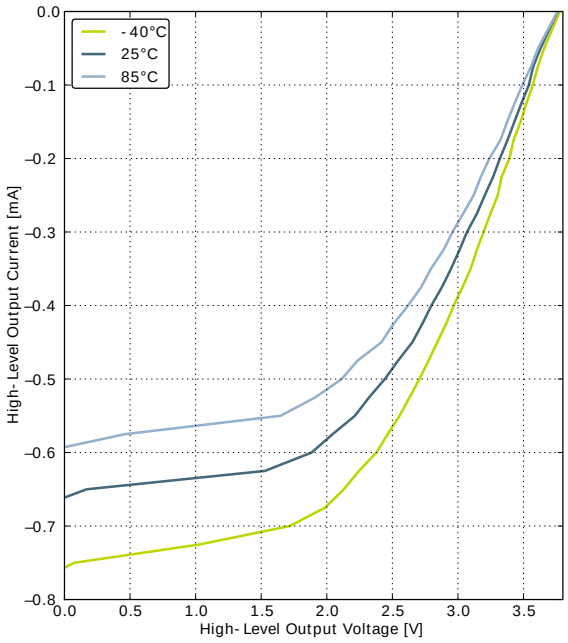
[1]Measured at 25°C

3.8 General Purpose Input Output

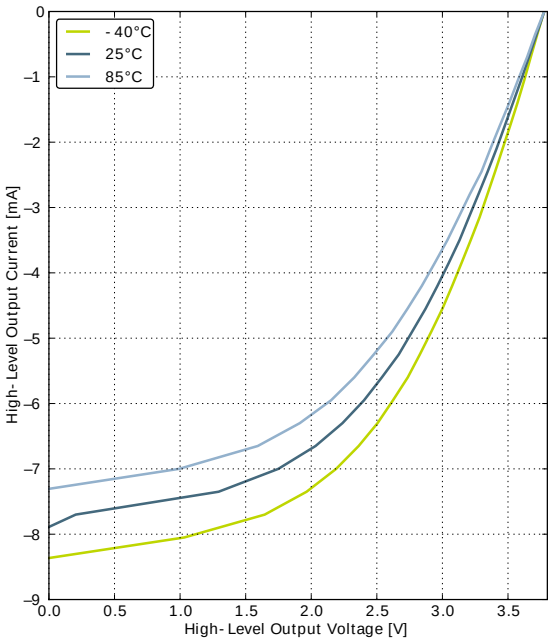
Table 3.7. GPIO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V_{IOIL}	Input low voltage				$0.30V_{DD}$	V
V_{IOIH}	Input high voltage		$0.70V_{DD}$			V
V_{IOOH}	Output high voltage (Production test condition = 3.0V, DRIVEMODE = STANDARD)	Sourcing 0.1 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		$0.80V_{DD}$		V
		Sourcing 0.1 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		$0.90V_{DD}$		V

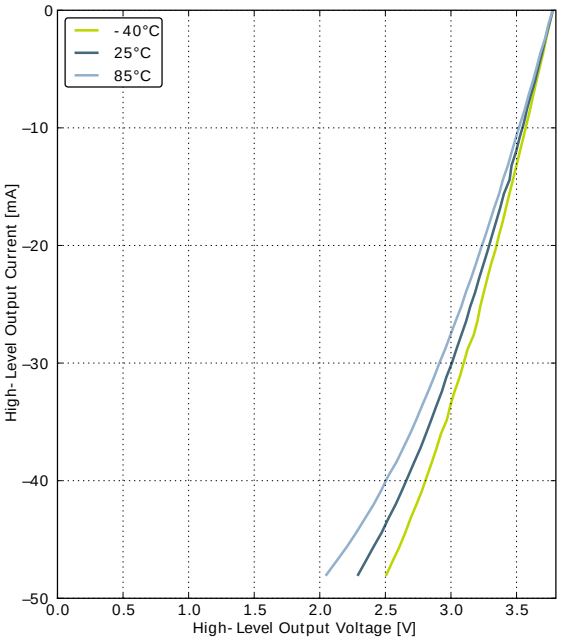
Figure 3.19. Typical High-Level Output Current, 3.8V Supply Voltage



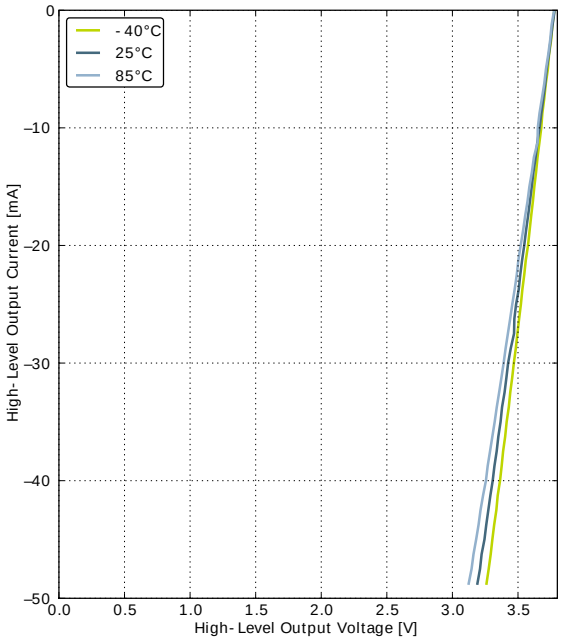
GPIO_Px_CTRL DRIVEMODE = LOWEST



GPIO_Px_CTRL DRIVEMODE = LOW



GPIO_Px_CTRL DRIVEMODE = STANDARD



GPIO_Px_CTRL DRIVEMODE = HIGH

Symbol	Parameter	Condition	Min	Typ	Max	Unit
		12 bit	13			ADC-CLK Cycles
t_{ADCACQ}	Acquisition time	Programmable	1		256	ADC-CLK Cycles
$t_{ADCACQVDD3}$	Required acquisition time for VDD/3 reference		2			µs
$t_{ADCSTART}$	Startup time of reference generator and ADC core in NORMAL mode			5		µs
	Startup time of reference generator and ADC core in KEEPADCWARM mode			1		µs
SNR_{ADC}	Signal to Noise Ratio (SNR)	1 MSamples/s, 12 bit, single ended, internal 1.25V reference		59		dB
		1 MSamples/s, 12 bit, single ended, internal 2.5V reference		63		dB
		1 MSamples/s, 12 bit, single ended, V_{DD} reference		65		dB
		1 MSamples/s, 12 bit, differential, internal 1.25V reference		60		dB
		1 MSamples/s, 12 bit, differential, internal 2.5V reference		65		dB
		1 MSamples/s, 12 bit, differential, 5V reference		54		dB
		1 MSamples/s, 12 bit, differential, V_{DD} reference		67		dB
		1 MSamples/s, 12 bit, differential, $2xV_{DD}$ reference		69		dB
		200 kSamples/s, 12 bit, single ended, internal 1.25V reference		62		dB
		200 kSamples/s, 12 bit, single ended, internal 2.5V reference		63		dB
		200 kSamples/s, 12 bit, single ended, V_{DD} reference		67		dB
		200 kSamples/s, 12 bit, differential, internal 1.25V reference		63		dB
		200 kSamples/s, 12 bit, differential, internal 2.5V reference		66		dB
		200 kSamples/s, 12 bit, differential, 5V reference		66		dB
		200 kSamples/s, 12 bit, differential, V_{DD} reference	63	66		dB

Symbol	Parameter	Condition	Min	Typ	Max	Unit
		1 MSamples/s, 12 bit, differential, 2xV_{DD} reference		75		dBc
		1 MSamples/s, 12 bit, differential, 5V reference		69		dBc
		200 kSamples/s, 12 bit, single ended, internal 1.25V reference		75		dBc
		200 kSamples/s, 12 bit, single ended, internal 2.5V reference		75		dBc
		200 kSamples/s, 12 bit, single ended, V_{DD} reference		76		dBc
		200 kSamples/s, 12 bit, differential, internal 1.25V reference		79		dBc
		200 kSamples/s, 12 bit, differential, internal 2.5V reference		79		dBc
		200 kSamples/s, 12 bit, differential, 5V reference		78		dBc
		200 kSamples/s, 12 bit, differential, V_{DD} reference	68	79		dBc
		200 kSamples/s, 12 bit, differential, 2xV_{DD} reference		79		dBc
$V_{ADCOFFSET}$	Offset voltage	After calibration, single ended	-4	0.3	4	mV
		After calibration, differential		0.3		mV
$TGRAD_{ADCTH}$	Thermometer output gradient			-1.92		mV/°C
				-6.3		ADC Codes/°C
DNL_{ADC}	Differential non-linearity (DNL)	V_{DD}= 3.0 V, external 2.5V reference	-1	±0.7	4	LSB
INL_{ADC}	Integral non-linearity (INL), End point method	V_{DD}= 3.0 V, external 2.5V reference		±1.2	±3	LSB
MC_{ADC}	No missing codes		11.999[1]	12		bits

[1]On the average every ADC will have one missing code, most likely to appear around 2048 ± n*512 where n can be a value in the set {-3, -2, -1, 1, 2, 3}. There will be no missing code around 2048, and in spite of the missing code the ADC will be monotonic at all times so that a response to a slowly increasing input will always be a slowly increasing output. Around the one code that is missing, the neighbour codes will look wider in the DNL plot. The spectra will show spurs on the level of -78dBc for a full scale input for chips that have the missing code issue.

The integral non-linearity (INL) and differential non-linearity parameters are explained in Figure 3.26 (p. 36) and Figure 3.27 (p. 36) , respectively.

Figure 3.26. Integral Non-Linearity (INL)

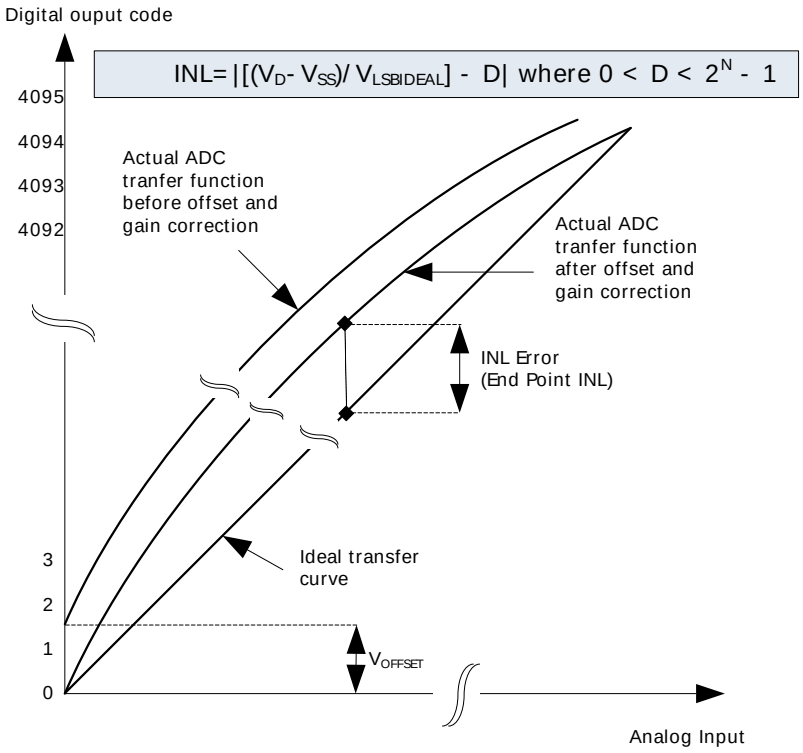


Figure 3.27. Differential Non-Linearity (DNL)

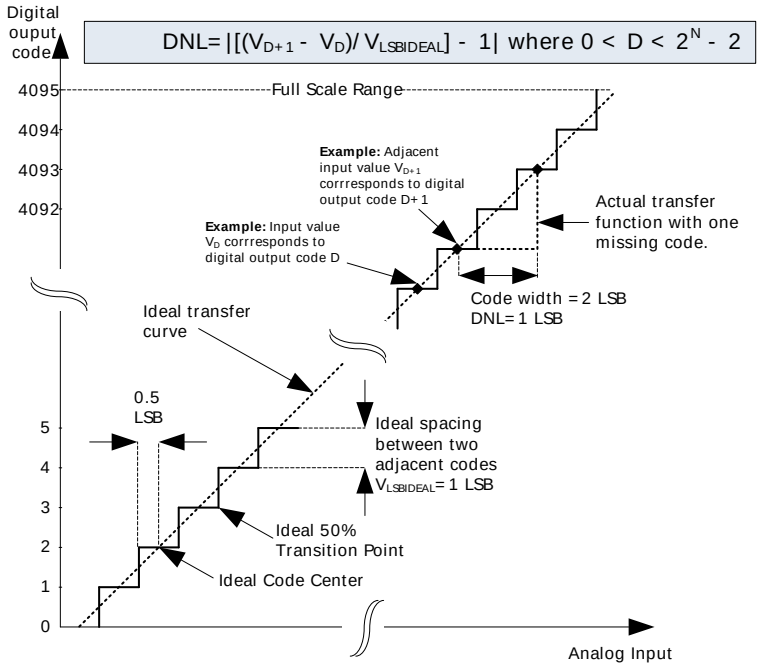
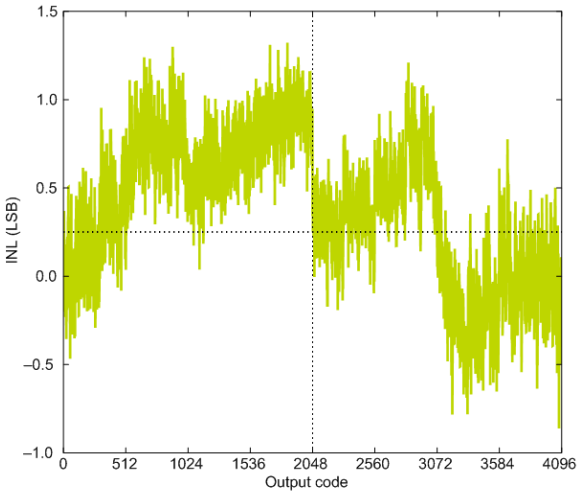
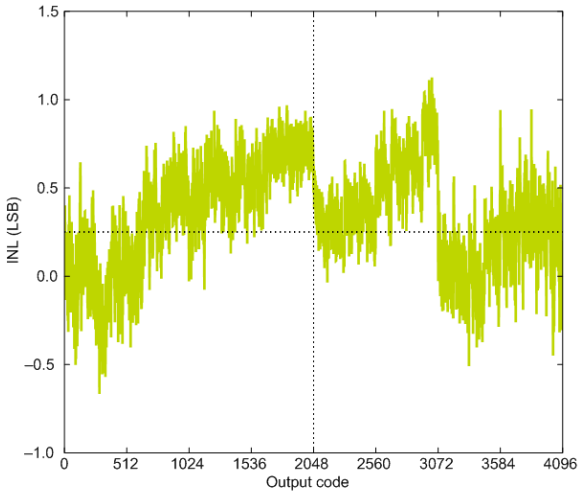


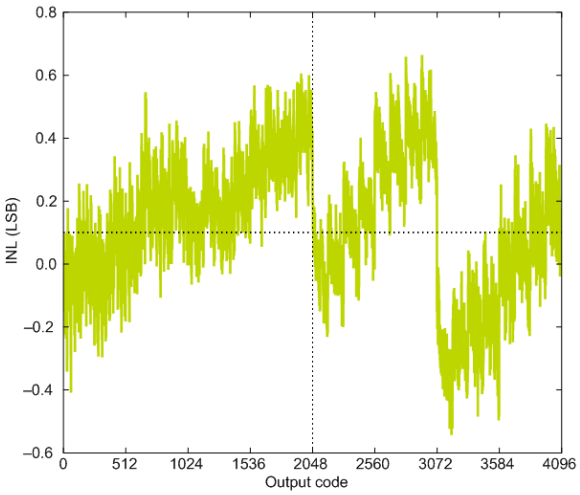
Figure 3.29. ADC Integral Linearity Error vs Code, Vdd = 3V, Temp = 25°C



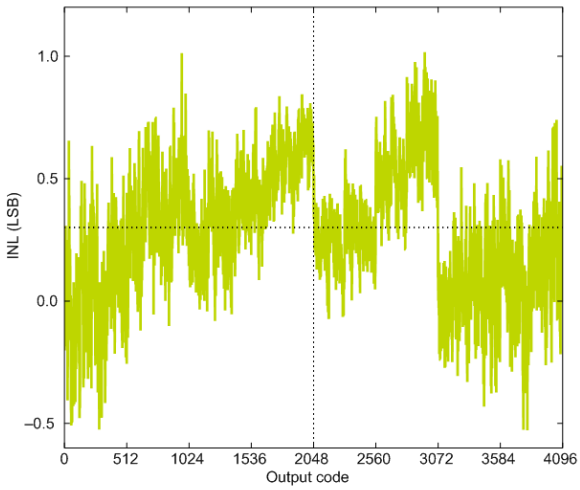
1.25V Reference



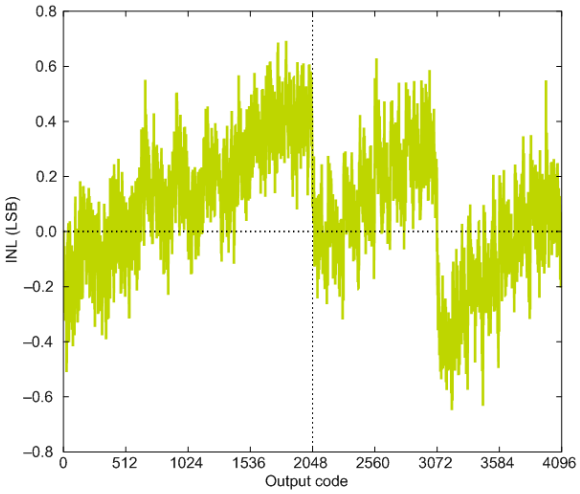
2.5V Reference



2XVDDVSS Reference

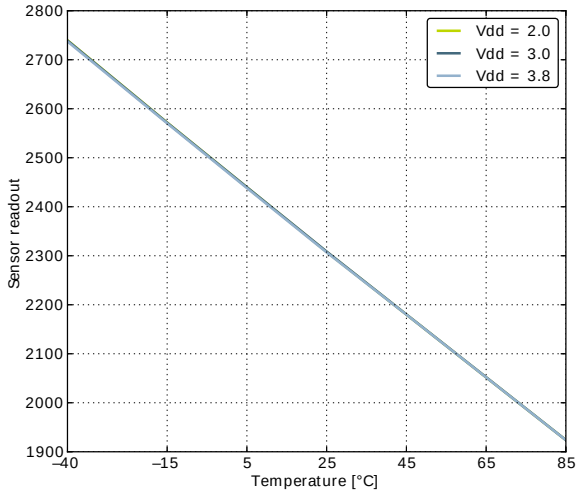


5VDIFF Reference



VDD Reference

Figure 3.33. ADC Temperature sensor readout



3.11 Current Digital Analog Converter (IDAC)

Table 3.15. IDAC Range 0 Source

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I_{IDAC}	Active current with STEPSEL=0x10	EM0, default settings		11.7		µA
		Duty-cycled		10		nA
I_{0x10}	Nominal IDAC output current with STEPSEL=0x10			0.84		µA
I_{STEP}	Step size			0.049		µA
I_D	Current drop at high impedance load	V_{IDAC_OUT} = V_{DD} - 100mV		0.73		%
TC_{IDAC}	Temperature coefficient	V_{DD} = 3.0V, STEPSEL=0x10		0.3		nA/°C
VC_{IDAC}	Voltage coefficient	T = 25 °C, STEPSEL=0x10		11.7		nA/V

Table 3.16. IDAC Range 0 Sink

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I_{IDAC}	Active current with STEPSEL=0x10	EM0, default settings		13.7		µA
I_{0x10}	Nominal IDAC output current with STEPSEL=0x10			0.84		µA
I_{STEP}	Step size			0.050		µA
I_D	Current drop at high impedance load	V_{IDAC_OUT} = 200 mV		0.16		%
TC_{IDAC}	Temperature coefficient	V_{DD} = 3.0 V, STEPSEL=0x10		0.2		nA/°C
VC_{IDAC}	Voltage coefficient	T = 25 °C, STEPSEL=0x10		12.5		nA/V

Table 3.17. IDAC Range 1 Source

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I_{IDAC}	Active current with STEPSEL=0x10	EM0, default settings		13.0		µA
		Duty-cycled		10		nA
I_{0x10}	Nominal IDAC output current with STEPSEL=0x10			3.17		µA
I_{STEP}	Step size			0.097		µA
I_D	Current drop at high impedance load	V_{IDAC_OUT} = V_{DD} - 100mV		0.79		%
TC_{IDAC}	Temperature coefficient	V_{DD} = 3.0 V, STEPSEL=0x10		0.7		nA/°C
VC_{IDAC}	Voltage coefficient	T = 25 °C, STEPSEL=0x10		38.4		nA/V

Table 3.18. IDAC Range 1 Sink

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I_{IDAC}	Active current with STEPSEL=0x10	EM0, default settings		17.9		µA
I_{0x10}	Nominal IDAC output current with STEPSEL=0x10			3.18		µA
I_{STEP}	Step size			0.098		µA
I_D	Current drop at high impedance load	V_{IDAC_OUT} = 200 mV		0.20		%
TC_{IDAC}	Temperature coefficient	V_{DD} = 3.0 V, STEPSEL=0x10		0.7		nA/°C
VC_{IDAC}	Voltage coefficient	T = 25 °C, STEPSEL=0x10		40.9		nA/V

Table 3.19. IDAC Range 2 Source

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I_{IDAC}	Active current with STEPSEL=0x10	EM0, default settings		16.2		µA
		Duty-cycled		10		nA
I_{0x10}	Nominal IDAC output current with STEPSEL=0x10			8.40		µA
I_{STEP}	Step size			0.493		µA
I_D	Current drop at high impedance load	V_{IDAC_OUT} = V_{DD} - 100mV		1.26		%
TC_{IDAC}	Temperature coefficient	V_{DD} = 3.0 V, STEPSEL=0x10		2.8		nA/°C
VC_{IDAC}	Voltage coefficient	T = 25 °C, STEPSEL=0x10		96.6		nA/V

Table 3.20. IDAC Range 2 Sink

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I_{IDAC}	Active current with STEPSEL=0x10	EM0, default settings		28.4		µA

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I_{0x10}	Nominal IDAC output current with STEPSEL=0x10			8.44		µA
I_{STEP}	Step size			0.495		µA
I_D	Current drop at high impedance load	V_{IDAC_OUT} = 200 mV		0.55		%
TC_{IDAC}	Temperature coefficient	V_{DD} = 3.0 V, STEPSEL=0x10		2.8		nA/°C
VC_{IDAC}	Voltage coefficient	T = 25 °C, STEPSEL=0x10		94.4		nA/V

Table 3.21. IDAC Range 3 Source

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I_{IDAC}	Active current with STEPSEL=0x10	EM0, default settings		18.3		µA
		Duty-cycled		10		nA
I_{0x10}	Nominal IDAC output current with STEPSEL=0x10			34.03		µA
I_{STEP}	Step size			1.996		µA
I_D	Current drop at high impedance load	V_{IDAC_OUT} = V_{DD} - 100 mV		3.18		%
TC_{IDAC}	Temperature coefficient	V_{DD} = 3.0 V, STEPSEL=0x10		10.9		nA/°C
VC_{IDAC}	Voltage coefficient	T = 25 °C, STEPSEL=0x10		159.5		nA/V

Table 3.22. IDAC Range 3 Sink

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I_{IDAC}	Active current with STEPSEL=0x10	EM0, default settings		62.9		µA
I_{0x10}	Nominal IDAC output current with STEPSEL=0x10			34.16		µA
I_{STEP}	Step size			2.003		µA
I_D	Current drop at high impedance load	V_{IDAC_OUT} = 200 mV		1.65		%
TC_{IDAC}	Temperature coefficient	V_{DD} = 3.0 V, STEPSEL=0x10		10.9		nA/°C
VC_{IDAC}	Voltage coefficient	T = 25 °C, STEPSEL=0x10		148.6		nA/V

Table 3.23. IDAC

Symbol	Parameter	Min	Typ	Max	Unit
$t_{IDACSTART}$	Start-up time, from enabled to output settled		40		µs

3.12 Analog Comparator (ACMP)

Table 3.24. ACMP

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V_{ACMPIN}	Input voltage range		0		V_{DD}	V
V_{ACMPCM}	ACMP Common Mode voltage range		0		V_{DD}	V
I_{ACMP}	Active current	BIASPROG=0b0000, FULLBIAS=0 and HALFBIAS=1 in ACMPn_CTRL register		0.1	0.4	µA
		BIASPROG=0b1111, FULLBIAS=0 and HALFBIAS=0 in ACMPn_CTRL register		2.87	15	µA
		BIASPROG=0b1111, FULLBIAS=1 and HALFBIAS=0 in ACMPn_CTRL register		195	520	µA
$I_{ACMPREF}$	Current consumption of internal voltage reference	Internal voltage reference off. Using external voltage reference		0		µA
		Internal voltage reference		5		µA
$V_{ACMPOFFSET}$	Offset voltage	BIASPROG= 0b1010, FULLBIAS=0 and HALFBIAS=0 in ACMPn_CTRL register	-12	0	12	mV
$V_{ACMPHYST}$	ACMP hysteresis	Programmable		17		mV
R_{CSRES}	Capacitive Sense Internal Resistance	CSRESSEL=0b00 in ACMPn_INPUTSEL		39		kOhm
		CSRESSEL=0b01 in ACMPn_INPUTSEL		71		kOhm
		CSRESSEL=0b10 in ACMPn_INPUTSEL		104		kOhm
		CSRESSEL=0b11 in ACMPn_INPUTSEL		136		kOhm
$t_{ACMPSTART}$	Startup time				10	µs

The total ACMP current is the sum of the contributions from the ACMP and its internal voltage reference as given in Equation 3.1 (p. 46) . $I_{ACMPREF}$ is zero if an external voltage reference is used.

Total ACMP Active Current

$$I_{ACMPTOTAL} = I_{ACMP} + I_{ACMPREF} \quad (3.1)$$

Alternate	LOCATION							
Functionality	0	1	2	3	4	5	6	Description
PCNT0_S1IN	PC14		PC1	PD7				Pulse Counter PCNT0 input number 1.
PRS_CH0	PA0		PC14					Peripheral Reflex System PRS, channel 0.
PRS_CH1	PA1		PC15					Peripheral Reflex System PRS, channel 1.
PRS_CH2	PC0		PE10					Peripheral Reflex System PRS, channel 2.
PRS_CH3	PC1		PE11					Peripheral Reflex System PRS, channel 3.
TIM0_CC0	PA0	PA0			PA0	PF0		Timer 0 Capture Compare input / output channel 0.
TIM0_CC1	PA1	PA1			PC0	PF1		Timer 0 Capture Compare input / output channel 1.
TIM0_CC2	PA2	PA2			PC1	PF2		Timer 0 Capture Compare input / output channel 2.
TIM1_CC0	PC13	PE10		PB7	PD6			Timer 1 Capture Compare input / output channel 0.
TIM1_CC1	PC14	PE11		PB8	PD7			Timer 1 Capture Compare input / output channel 1.
TIM1_CC2	PC15	PE12		PB11	PC13			Timer 1 Capture Compare input / output channel 2.
US1_CLK	PB7		PF0	PC15				USART1 clock input / output.
US1_CS	PB8		PF1	PC14				USART1 chip select input / output.
US1_RX	PC1		PD6	PD6				USART1 Asynchronous Receive. USART1 Synchronous mode Master Input / Slave Output (MISO).
US1_TX	PC0		PD7	PD7				USART1 Asynchronous Transmit.Also used as receive input in half duplex communication. USART1 Synchronous mode Master Output / Slave Input (MOSI).

4.3 GPIO Pinout Overview

The specific GPIO pins available in *EFM32ZG210* is shown in Table 4.3 (p. 54). Each GPIO port is organized as 16-bit ports indicated by letters A through F, and the individual pin on this port is indicated by a number from 15 down to 0.

Table 4.3. GPIO Pinout

Port	Pin 15	Pin 14	Pin 13	Pin 12	Pin 11	Pin 10	Pin 9	Pin 8	Pin 7	Pin 6	Pin 5	Pin 4	Pin 3	Pin 2	Pin 1	Pin 0
Port A	-	-	-	-	-	-	-	-	-	-	-	-	-	PA2	PA1	PA0
Port B	-	PB14	PB13	-	PB11	-	-	PB8	PB7	-	-	-	-	-	-	-
Port C	PC15	PC14	PC13	-	-	-	-	-	-	-	-	-	-	-	PC1	PC0
Port D	-	-	-	-	-	-	-	-	PD7	PD6	PD5	PD4	-	-	-	-
Port E	-	-	PE13	PE12	PE11	PE10	-	-	-	-	-	-	-	-	-	-
Port F	-	-	-	-	-	-	-	-	-	-	-	-	-	PF2	PF1	PF0

5 PCB Layout and Soldering

5.1 Recommended PCB Layout

Figure 5.1. QFN32 PCB Land Pattern

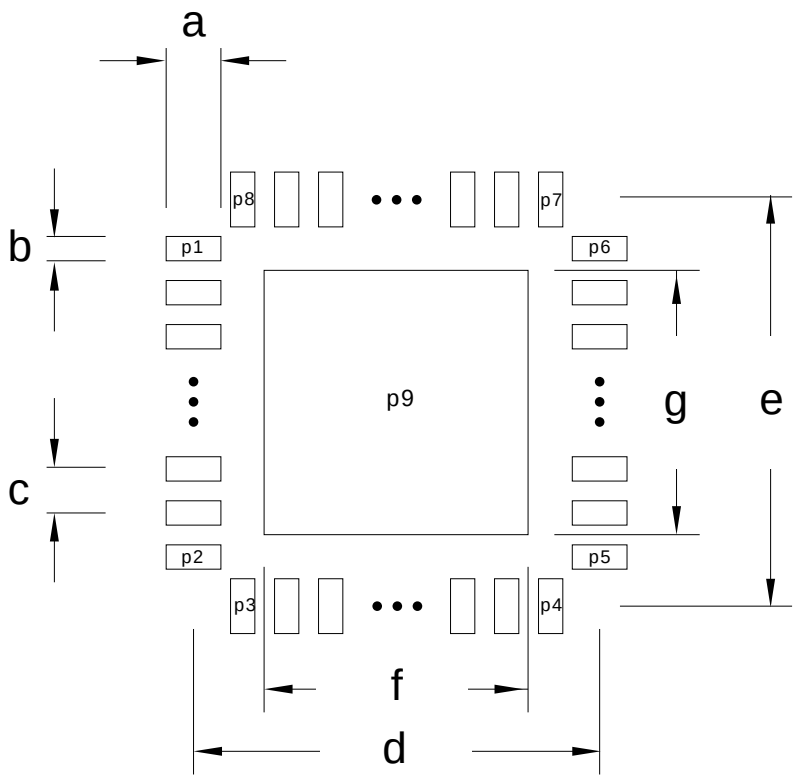


Table 5.1. QFN32 PCB Land Pattern Dimensions (Dimensions in mm)

Symbol	Dim. (mm)	Symbol	Pin number	Symbol	Pin number
a	0.80	P1	1	P6	24
b	0.35	P2	8	P7	25
c	0.65	P3	26	P8	32
d	6.00	P4	16	P9	33
e	6.00	P5	17	-	-
f	4.40	-	-	-	-
g	4.40	-	-	-	-

Figure 5.3. QFN32 PCB Stencil Design

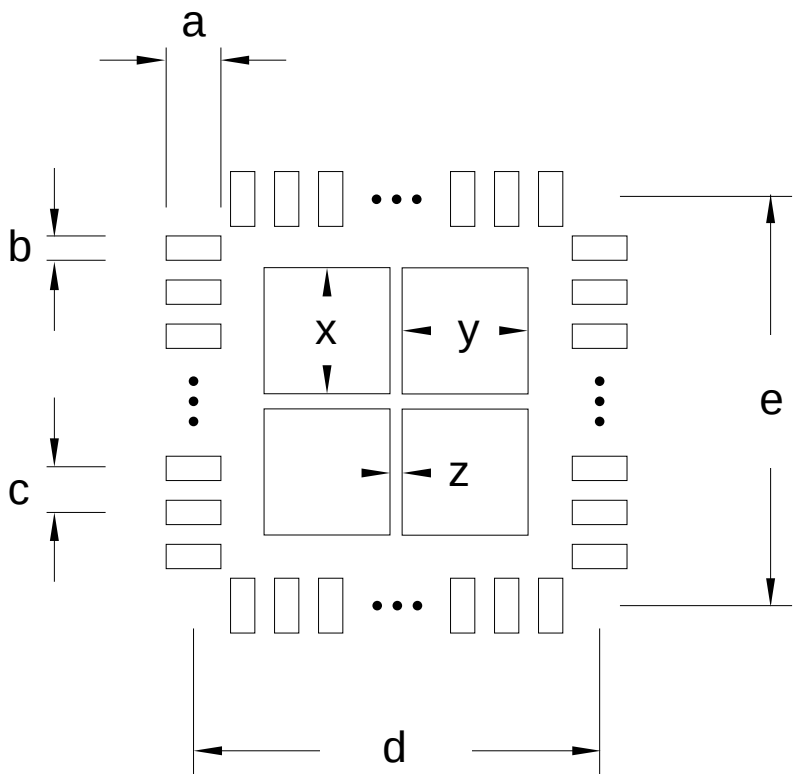


Table 5.3. QFN32 PCB Stencil Design Dimensions (Dimensions in mm)

Symbol	Dim. (mm)
a	0.70
b	0.25
c	0.65
d	6.00
e	6.00
x	1.30
y	1.30
z	0.50

1. The drawings are not to scale.
2. All dimensions are in millimeters.
3. All drawings are subject to change without notice.
4. The PCB Land Pattern drawing is in compliance with IPC-7351B.
5. Stencil thickness 0.125 mm.
6. For detailed pin-positioning, see Figure 4.2 (p. 55) .

5.2 Soldering Information

The latest IPC/JEDEC J-STD-020 recommendations for Pb-Free reflow soldering should be followed.

The packages have a Moisture Sensitivity Level rating of 3, please see the latest IPC/JEDEC J-STD-033 standard for MSL description and level 3 bake conditions. Place as many and as small as possible vias underneath each of the solder patches under the ground pad.

B Contact Information

Silicon Laboratories Inc.
400 West Cesar Chavez
Austin, TX 78701

Please visit the Silicon Labs Technical Support web page:
http://www.silabs.com/support/pages/contacttechnicalsupport.aspx
and register to submit a technical support request.

List of Tables